

This listing of claims will replace all prior versions and listings of claims in the application.

Listing of Claims:

1(original). An active organic light emitting diode display structure comprises:
a glass substrate;
an active component layer, disposed on the glass substrate;
an intermediate insulate layer, disposed on the top of the active component layer;
a color filter area, disposed on part of the surface of the intermediate insulate layer;
an electrical conducting layer, disposed above the color filter area;
a black matrix layer, disposed on the top surface of the electrical conducting layer, and cover margins of the color filter area;
an organic light emitting diode layer, disposed on the black matrix layer; and
a cathode ray layer, disposed in the organic light emitting diode layer.

2(canceled).

3(original). The active organic light emitting diode display structure of claim 1, wherein the active component layer is a buffer layer having poly-Si thin film transistors (poly-Si TFTs).

4(original). The active organic light emitting diode display structure of claim 1, wherein the color filter area is coated on an area of the surface of the intermediate insulate layer.

5(original). The active organic light emitting diode display structure of claim 1, wherein the electrical conducting layer is an indium tin oxide (ITO) layer.

6(original). The active organic light emitting diode display structure of claim 1, wherein the black matrix layer is a metal thin film.

7(original). The active organic light emitting diode display structure of claim 1, wherein the black matrix layer is a black photo resist thin film.

8(original). The active organic light emitting diode display structure of claim 1, wherein the black matrix layer is disposed on the top surface of the electrical conducting layer, the black matrix layer has an opening, the opening is located above the color filter area, the area of the opening is lightly smaller than the area of the color filter area, and the black matrix layer covers margins of the color filter area as well as the non color filter area.

9(currently amended). The active organic light emitting diode display structure of claim 8, wherein the organic light emitting diode is white organic light emitting diode.

10(new). The active organic light emitting diode display structure of claim 1, wherein the entirety of the black matrix layer is disposed on the top surface of the electrical conducting layer, the black matrix layer has an opening, the opening is located above the color filter area, the area of the opening is lightly smaller than the area of the color filter area, and the black matrix layer covers margins of the color filter area as well as the non color filter area.

11(new). The active organic light emitting diode display structure of claim 1, wherein the electrical conducting layer is disposed on the intermediate insulate layer by sputtering.

12(new). The active organic light emitting diode display structure of claim 1, wherein the active component layer is a buffer layer having poly-Si thin film transistors (poly-Si TFTs); the color filter area is coated on an area of the surface of the

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intermediate insulate layer; the electrical conducting layer is an indium tin oxide (ITO) layer; the black matrix layer is a metal thin film or a black photo resist thin film; the organic light emitting diode is white organic light emitting diode; the entirety of the black matrix layer is disposed on the top surface of the electrical conducting layer, the black matrix layer has an opening, the opening is located above the color filter area, the area of the opening is lightly smaller than the area of the color filter area, and the black matrix layer covers margins of the color filter area as well as the non color filter area; and the electrical conducting layer is disposed on the intermediate insulate layer by sputtering.